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FQA65N20

N-Channel QFET® MOSFET

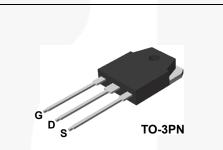
200 V, 65 A, 32 mΩ

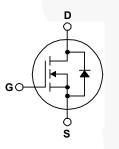
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 65 A, 200 V, $R_{DS(on)} = 32 \text{ m}\Omega \text{ (Max.)} @ V_{GS} = 10 \text{ V}, I_D = 32.5 \text{ A}$
- Low Gate Charge (Typ. 170 nC)
- Low Crss (Typ. 90 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQA65N20	Unit	
V _{DSS}	Drain-Source Voltage		200	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}$ C	C)	65	A	
	- Continuous (T _C = 100	°C)	41	A	
I _{DM}	Drain Current - Pulsed	(Note 1)	260	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1010	mJ	
I _{AR}	Avalanche Current	(Note 1)	65	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	31	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	te 3) 5.5		
P _D	Power Dissipation ($T_C = 25^{\circ}C$)	310	W		
	- Derate above 25°C		2.5	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Ran	ge	-55 to +150	°C	
ΤL	Maximum Lead Temperature for Solderin 1/8" from Case for 5 Seconds	g,	300	°C	

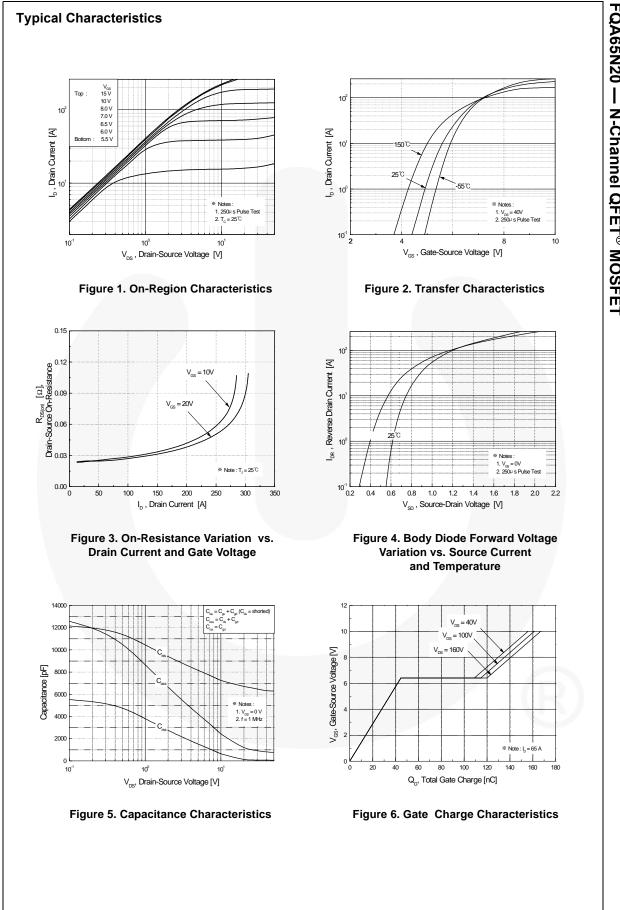
Thermal Characteristics

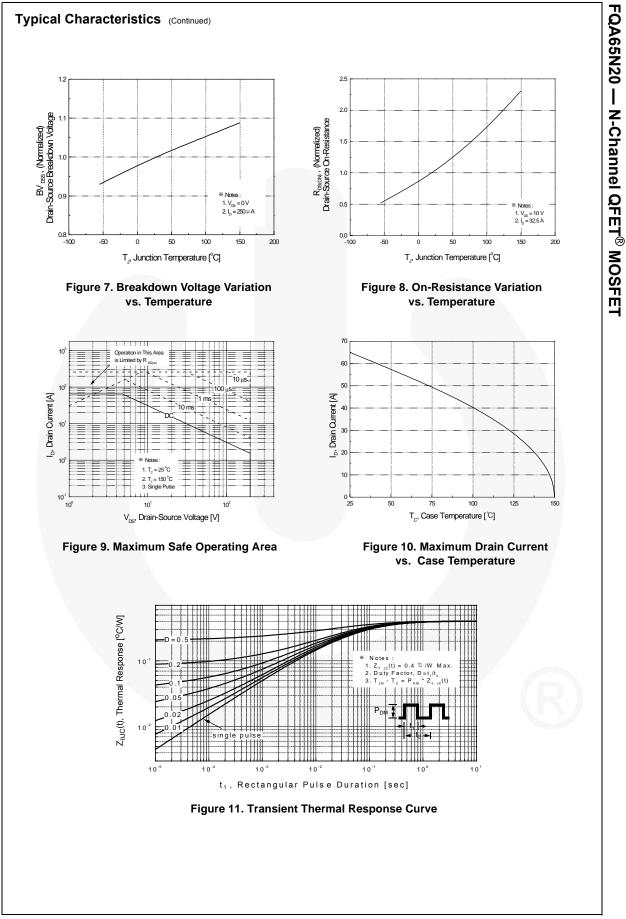
Symbol	Parameter	FQA65N20	Unit °C/W °C/W	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.4		
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ	0.24		
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

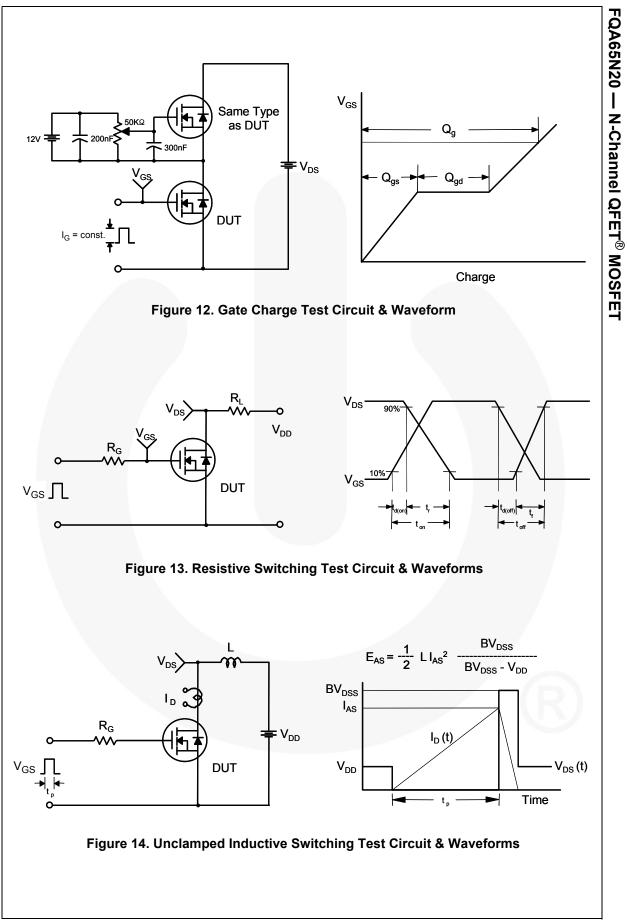
May 2014

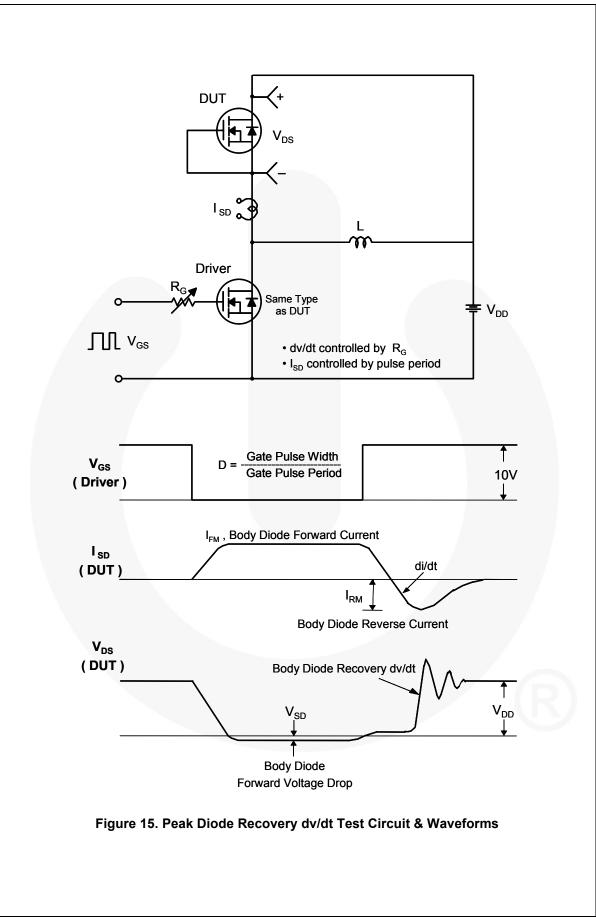
Part Nu	ımber	Top Mark	Pack	kage Packing Metho		thod	Reel Size		Tape Width		Quantity
FQA65N20		FQA65N20	TO-3	TO-3PN Tube		N/A	4	N/A		30 units	
loctri	cal Ch	aracteristics	т. 05 ⁰ 0 ни		view works of						
Symbol		Parameter	1 _C = 25 C uni	ess otherv	Test Conditio	ons		Min.	Тур.	Max.	Unit
) Off Cha	racteris	tics		4						ļ	-
BV _{DSS}		urce Breakdown Vol	ade	V _{GS} =	0 V, I _D = 250 μ/	Ą		200			V
BVDSS	Breakdown Voltage Temperature			$I_D = 250 \mu$ A, Referenced to 25°C				0.15		V/°C	
ΔT_{J}	Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward		$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 160 \text{ V}, T_{C} = 125^{\circ}\text{C}$								
DSS								1 10	μΑ		
GSSF			$V_{DS} = 160 \text{ V}, T_{C} = 123 \text{ C}$ $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$						100	μA nA	
GSSF		Gate-Body Leakage Current, Reverse			$-30 \text{ V}, \text{ V}_{\text{DS}} = 0 \text{ V}$					-100	nA
		, ,		00							
	Gate Th			Vac -	V _{GS} , I _D = 250 μ	A		3.0		5.0	V
/ _{GS(th)} R _{DS(on)}		eshold Voltage		_				3.0			-
20(01)	On-Resis	stance		00	10 V, I _D =32.5 A				0.025	0.032	
FS	Forward	Transconductance	_	$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 32.5 \text{ A}$					58		S
)vnami	ic Chara	cteristics									
viss		pacitance	_	V	$25 \sqrt{1} = 0$	/			6600	7900	pF
Soss		apacitance			V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			1000	1200	pF	
Prss	-	Transfer Capacitanc	е					90	120	pF	
										1	
		racteristics							100	050	-
d(on)		Delay Time	_	$V_{DD} = 100 \text{ V}, \text{ I}_{D} = 65 \text{ A},$			120	250	ns		
r 		Rise Time		$R_{G} = 2$	25 Ω				640 340	770 690	ns
d(off)		Delay Time Fall Time				(N	lote 4)		275	560	ns
λ _g		te Charge		V	460.1/1 65.4	^			170	200	nC
×g Σ _{gs}		urce Charge		-	V _{DS} = 160 V, I _D = 65 A, V _{GS} = 10 V				45		nC
λ _{gd}		ain Charge		VGS -	10 0	(N	lote 4)		75		nC
gu							·				
		oide Character				ngs			1		1
S				Diode Forward Current						65	A
SM		n Pulsed Drain-Sour								260	A
/ _{SD}		urce Diode Forward	Voltage		0 V, $I_S = 65 A$					1.5	V
rr		Recovery Time			0 V, I _S = 65 A, t = 100 A/μs				195		ns
ג ^{ער}	Reverse	Recovery Charge		u _F /u	$t = 100 A/\mu s$				1.4		μC
L = 0.36 mH I _{SD} ≤ 65 A, 0	H, I _{AS} = 65 A, ' di/dt ≤ 300 A/µ	vidth limited by maximum ju $V_{\text{DD}} = 50 \text{ V}, R_{\text{G}} = 25 \Omega$, star Js, $V_{\text{DD}} \le 8V_{\text{DSS}}$, starting TJ of operating temperature.	ting T _J = 25°C								

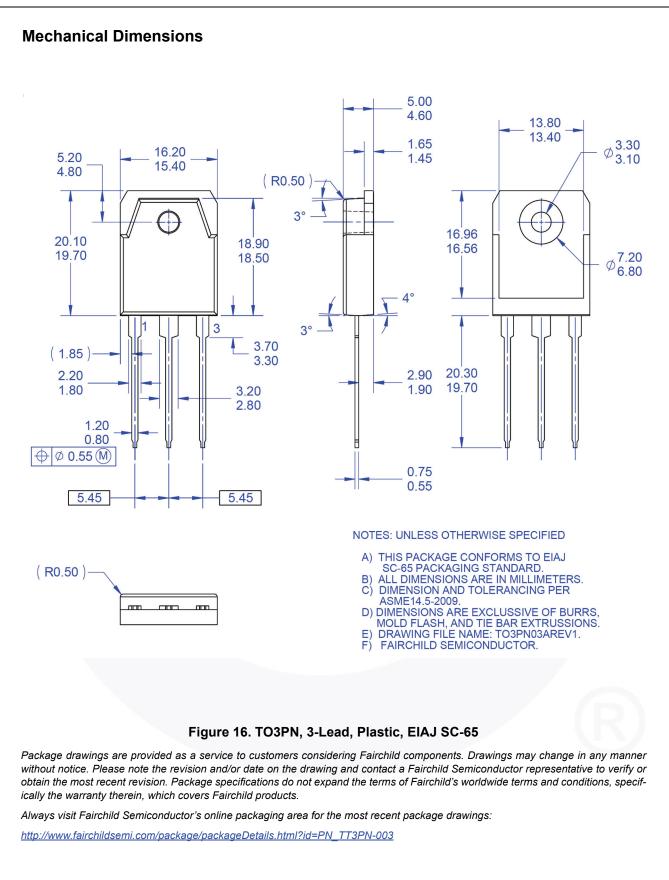
FQA65N20 — N-Channel QFET[®] MOSFET













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